

AMENDMENTS TO THE CLAIMS:

Please amend claims 1, 3 – 6, and 13 – 18, and add new claims 19 – 21 as indicated below. This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (Currently Amended) A method of manufacturing a semiconductor device, comprising:

- ~~a step of~~ forming an insulating film on a semiconductor substrate;
- ~~a step of~~ forming a groove in the insulating film;
- ~~a step of~~ filling the groove with a wiring material;
- ~~a step of~~ performing CMP to form a filled wiring;
- ~~a step of~~ etching the filled wiring material to thereby form a recess;
- ~~a step of~~ depositing a cap film on the recess formed by etching the wiring material;
- ~~a first polishing step of~~ performing a first polishing operation at selectivity of R1 (= removal rate for the cap film/removal rate for the insulating film); and
- ~~a second polishing step of~~ performing a second polishing operation at selectivity of R2 (= removal rate for the cap film/removal rate for the insulating film),

wherein each of the first polishing ~~step~~ operation and the second polishing ~~step~~ operation is performed by using a slurry having a condition of $R1 > R2$.

2. (Original) A method of manufacturing a semiconductor device according to claim 1, wherein a depth of the recess formed by etching the wiring material is larger than the thickness of the cap film.

3. (Currently Amended) A method of manufacturing a semiconductor device according to claim 1, wherein R1 in the first polishing ~~step~~ operation is equal to or larger than 1 and R2 in the second polishing ~~step~~ operation is equal to or smaller than 1.

4. (Currently Amended) A method of manufacturing a semiconductor device according to ~~any one of claims 1 to 3~~ claim 1, wherein a main component of the cap film is [[any]] selected from the group consisting of Ti, Ta, Nb, W, Cr, V, Pt, and Ru, a nitride, an oxide, a boride, and an alloy of any of the elements, and a mixture of the elements.

5. (Currently Amended) A method of manufacturing a semiconductor device according to ~~any one of claims 1 to 3~~ claim 1, wherein a main component of the cap film is [[any]] selected from the group consisting of Si, an Si oxide and an Si nitride, or the cap film is a fluorine-doped oxide film.

6. (Currently Amended) A method of manufacturing a semiconductor device according to ~~any one of claims 1 to 3~~ claim 1, wherein a main component of the wiring material is [[any]] selected from the group consisting of Al, Cu, W, Ru, Ag, Mo, and Si, a nitride, an oxide, a boride and an alloy of any of the elements, and a mixture of any of the elements.

7. – 12. (Canceled)

13. (Currently Amended) A method of manufacturing a semiconductor device according to claim 2, wherein a main component of the cap film is [[any]] selected from the group consisting of Ti, Ta, Nb, W, Cr, V, Pt, and Ru, a nitride, an oxide, a boride, and an alloy of any of the elements, and a mixture of the elements.

14. (Currently Amended) A method of manufacturing a semiconductor device according to claim 2, wherein a main component of the cap film is [[any]] selected from the group consisting of Si, an Si oxide and an Si nitride, or the cap film is a fluorine-doped oxide film or poly-methyl-siloxane.

15. (Currently Amended) A method of manufacturing a semiconductor device according to claim 2, wherein a main component of the wiring material is [[any]] selected from the group consisting of Al, Cu, W, Ru, Ag, Mo, and Si, a nitride, an oxide, a boride and an alloy of any of the elements, and a mixture of any of the elements.

16. (Currently Amended) A method of manufacturing a semiconductor device according to claim 3, wherein a main component of the cap film is [[any]] selected from the group consisting of Ti, Ta, Nb, W, Cr, V, Pt, and Ru, a nitride, an oxide, a boride, and an alloy of any of the elements, and a mixture of the elements.

17. (Currently Amended) A method of manufacturing a semiconductor device according to claim 3, wherein a main component of the cap film is [[any]] selected from the group consisting of Si, an Si oxide and an Si nitride, or the cap film is a fluorine-doped oxide film or poly-methyl-siloxane.

18. (Currently Amended) A method of manufacturing a semiconductor device according to claim 3, wherein a main component of the wiring material is [[any]] selected from the group consisting of Al, Cu, W, Ru, Ag, Mo, and Si, a nitride, an oxide, a boride and an alloy of any of the elements, and a mixture of any of the elements.

19. (New) A method of manufacturing a semiconductor device according to claim 2, wherein the first polishing operation is performed to remove a portion of the cap film, which is on the insulating film outside the recess.

20. (New) A method of manufacturing a semiconductor device according to claim 19, wherein the first polishing operation is performed to leave a step between the cap film in the recess and the insulating film.

21. (New) A method of manufacturing a semiconductor device according to claim 20, wherein the second polishing operation is performed to remove the step between the cap film in the recess and the insulating film.